# International **IOR** Rectifier

## 8.0 Amps Single Phase Full Wave

#### Features

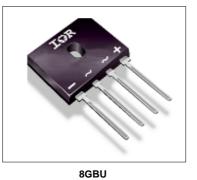
- Diode chips are glass passivated
- Suitable for Universal hole mounting
- Easy to assemble & install on P.C.B.
- High Surge Current Capability
- High Isolation between terminals and molded case (1500 V<sub>RMS</sub>)
- Lead free terminals solderable as per MIL-STD-750 Method 2026
- Terminals suitable for high temperature soldering at 260°C for 8-10 secs
- UL E160375 approved

#### Description

These GBU Series of Single Phase Bridges consist of four glass passivated silicon junction connected as a Full Wave Bridge. These four junctions are encapsulated by plastic molding technique. These Bridges are mainly used in Switch Mode power supply and in industrial and consumer equipment.

#### **Major Ratings and Characteristics**

Parameters		8GBU	Units	
I <sub>o</sub>		8	А	
	@ T <sub>c</sub>	100	°C	
I <sub>FSM</sub>	@50Hz	200	A	
	@ 60Hz	210	А	
l <sup>2</sup> t	@ 50Hz	200	A <sup>2</sup> s	
	@ 60Hz	184	A <sup>2</sup> s	
V <sub>RRM</sub>	range	50 to 1200	V	
TJ		- 55 to 150	°C	



# Bridge Rectifier

**8GBU Series** 

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#### **ELECTRICAL SPECIFICATIONS**

#### Voltage Ratings

	Voltage	T G G WI	V <sub>RSM</sub> , max non-repetitive	V <sub>RMS</sub> , max RMS	I <sub>RRM</sub> max.	I <sub>RRM</sub> max.
Type number	Code	peak rev. voltage	peak rev. voltage		@ rated $V_{\text{RRM}}$	
		T <sub>J</sub> = T <sub>J</sub> max.	T_= T_max.	T <sub>J</sub> = T <sub>J</sub> max.	T_= 25°C	T <sub>J</sub> =150°C
	V	Ň	V	V	μA	μA
8GBU	005	50	80	35	5	400
	01	100	150	70	5	400
	02	200	300	140	5	400
	04	400	500	280	5	400
	06	600	725	420	5	400
	08	800	900	560	5	400
	10	1000	1100	700	5	400
	12	1200	1300	850	5	400

#### **Forward Conduction**

	Parameters	8GBU	Unit	Conditions	
I <sub>o</sub>	Maximum DC output current	8.0	A	T <sub>C</sub> =100°C, Resisti	ve& inductive load
		6.4		T <sub>c</sub> =100°C, Capacitive load	
I <sub>FSM</sub>	Maximum peak, one-cycle	200		t = 10ms	
	non-repetitive surge current,				
	following any rated load condition	210		t = 8.3ms	T <sub>J</sub> =150°C
	and with rated $V_{\ensuremath{RRM}}$ reapplied				
l <sup>2</sup> t	Maximum I <sup>2</sup> t for fusing,	200	A <sup>2</sup> s	t = 10ms	
	initial T <sub>J</sub> =T <sub>J</sub> max	184		t = 8.3ms	
V <sub>FM</sub>	Maximum peak forward voltage per diode	1.0	V	T <sub>J</sub> =25°C, I <sub>FM</sub> =8A	
I <sub>RM</sub>	Typical peak reverse leakage	5.0	μA	T <sub>J</sub> = 25℃, 100%∖	/ <sub>RRM</sub>
	current per diode	400		T <sub>J</sub> =150 °C, 100% V <sub>RRM</sub>	
V <sub>RRM</sub>	Maximum repetitive peak	50 to 1200	V		
	reverse voltage range				

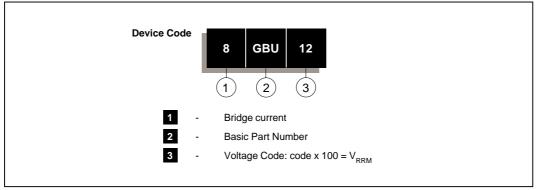
#### **Thermal and Mechanical Specifications**

	Parameters	8GBU	Unit	Conditions
T <sub>J</sub> T <sub>stg</sub>	Operating and storage temperature range	-55 to 150	°C	
R <sub>thJC</sub>	Max. thermal resistance junction to case	2.2	°C/W	DC rated current through bridge (1)
R <sub>thJA</sub>	Thermal resistance, junction to ambient	21	°C/W	DC rated current through bridge (1)
W	Approximateweight	4(0.14)	g(oz)	
Т	MountingTorque	1.0	Nm	Bridge to Heatsink
		9.0	Lb.in	

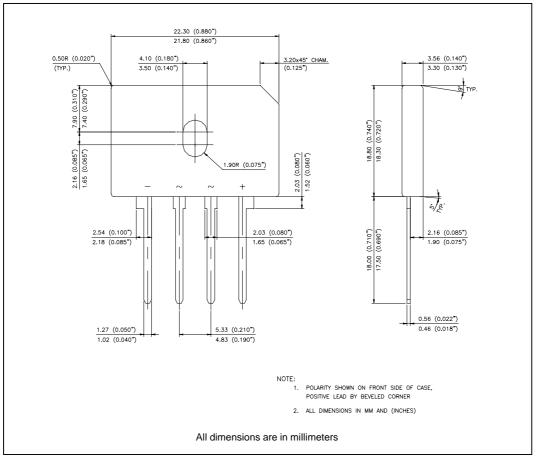
Note (1): Bridge mounted on Aluminun heat sink of dim 82x82x3.0mm, use silicon thermal compound heat transfer and bolt down using 3mm screw

Bulletin I2719 rev. F 11/02

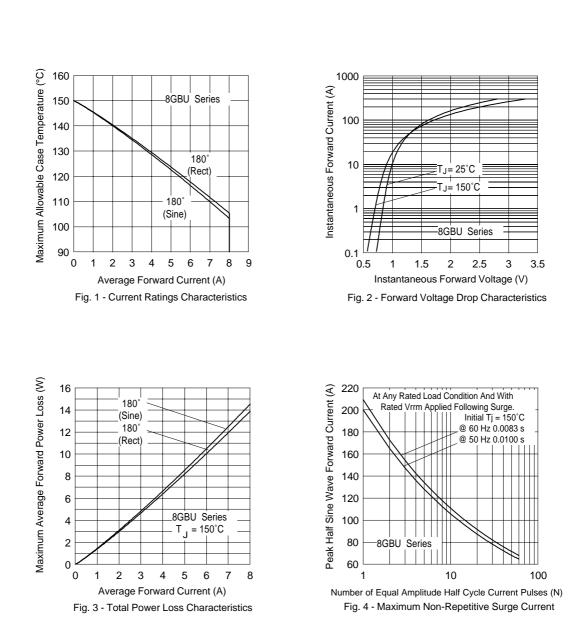
#### **Ordering Information Table**



#### **Outline Table**



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### International **tor** Rectifier

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**8GBU Series** 

Bulletin I2719 rev. F 11/02

International	8GBU Series
<b>IOR</b> Rectifier	Bulletin I2719 rev. F 11/02

Data and specifications subject to change without notice. This product has been designed and qualified for Multiple Level. Qualification Standards can be found on IR's Web site.



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